

## Patent Abstracts of Japan

PUBLICATION NUMBER : 08107156  
PUBLICATION DATE : 23-04-96

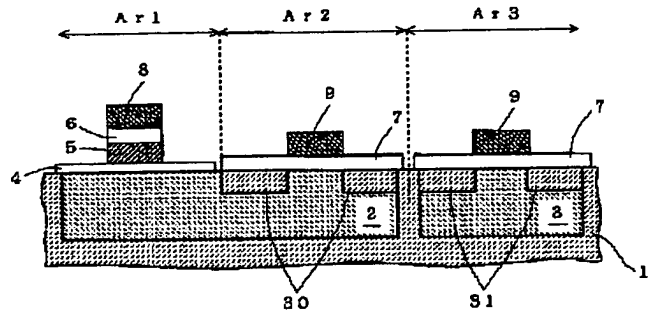
APPLICATION DATE : 05-10-94  
APPLICATION NUMBER : 06241421

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INT.CL. : H01L 21/8247 H01L 29/788 H01L  
29/792 H01L 27/115

TITLE : MANUFACTURE OF NON-VOLATILE  
SEMICONDUCTOR STORAGE DEVICE



**ABSTRACT :** **PURPOSE:** To dispense with a process for forming a peripheral transistor by a method wherein the source/drain of a second MOS transistor is formed using a floating gate formed on a semiconductor region, which contains a region where the source/drain of a first MOS transistor is formed, as a mask.

**CONSTITUTION:** A floating gate 5 is formed on a semiconductor region, which includes an N region where a P-region that forms the source/drain region of a P-channel MOS transistor is formed, using an ONO film 6 as a mask, wherein the ONO film 6 is etched through a control gate 8 as a mask. Then, the control gate 8 and the gate 9 of cells are patterned using the floating gate 5 as a mask, and then N-type impurities are injected into all the surface of a substrate for the formation of an N<sup>+</sup> region. At this point, the N<sup>+</sup> region is formed with the gates 9 of an N-channel MOS transistor and a P-channel MOS transistor as a mask.

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